

High Brightness 6.4×4.0 4 Bar LED Arrays

SBD-446

GENERAL DESCRIPTION

The SBD-446 series of 4 bar light emitting diode arrays has been developed for level meters and other linear display and available in red, orange, green and yellow emitting colors.

The standard units are constructed with black or gray face and milky white segment colors.

FEATURES

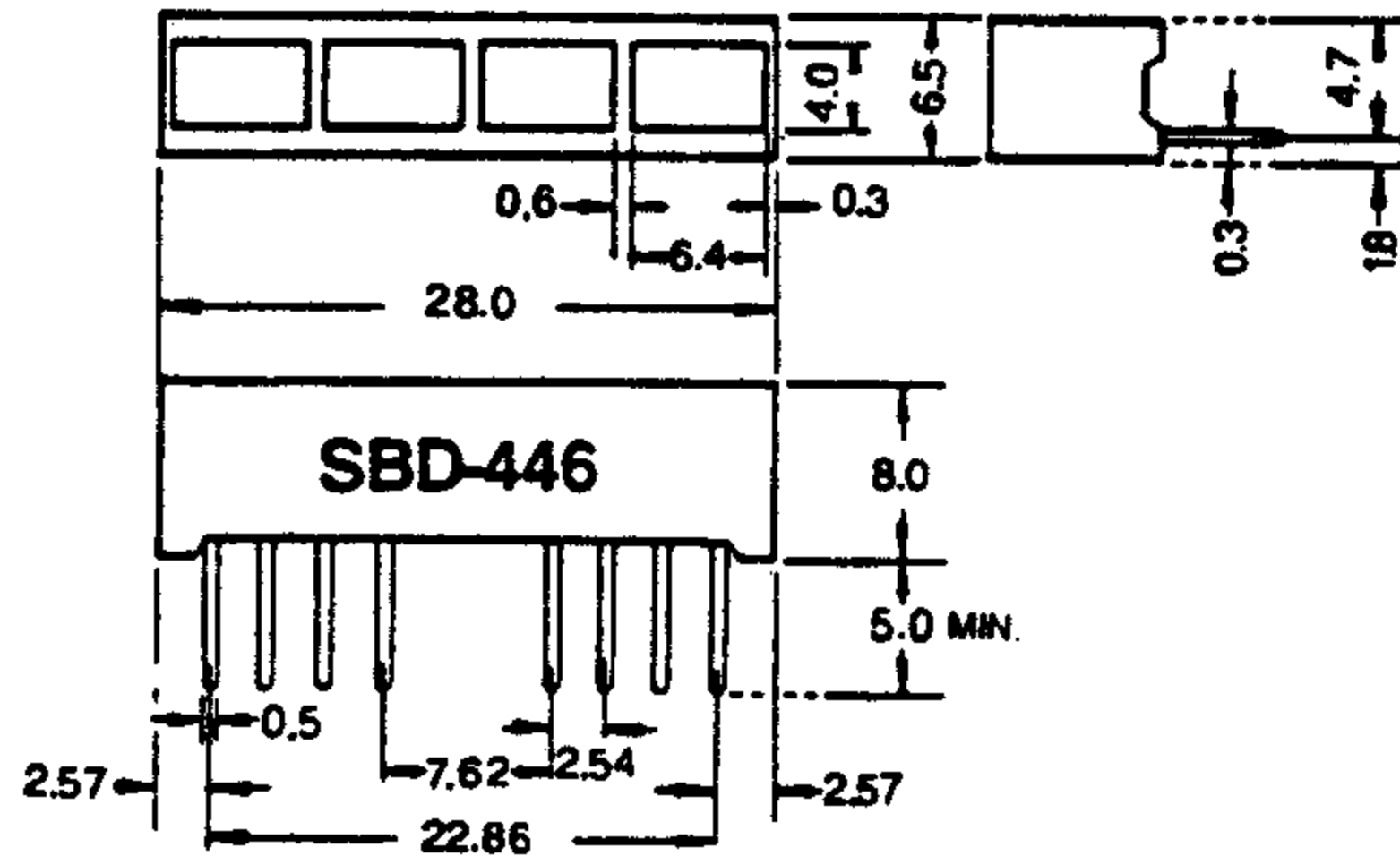
1. High brightness
2. Low power consumption; Directly drive with IC
3. Solid state stability; Long-operation life
4. Could be matched to SBD-646 for 10 bars

Actual size

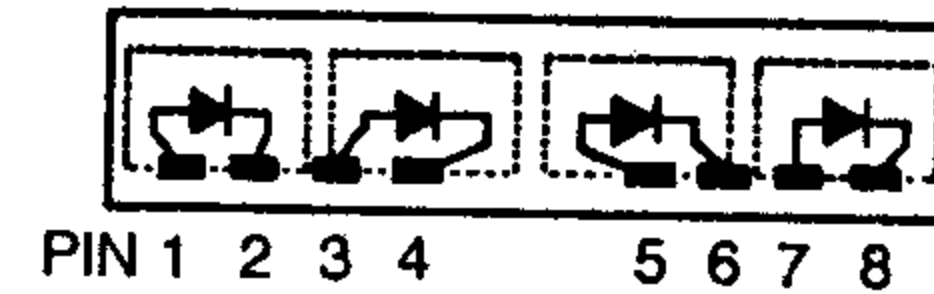


PACKAGE DIMENSIONS AND CONNECTIONS GUIDE

SCALE 1:1 (mm)



(Top View)



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Red SBD 446R (GaP)

Absolute Maximum Ratings ($T_a=25^\circ\text{C}$)

Power dissipation/Total	160	mW
Power dissipation/Chip	40	mW
Forward current	20	mA
Peak forward current	60*	mA
Reverse voltage	4	V
Operating temperature	-25 ~ +85	$^\circ\text{C}$
Storage temperature	-55 ~ +100	$^\circ\text{C}$

Green SBD 446G (GaP)

Absolute Maximum Ratings ($T_a=25^\circ\text{C}$)

Power dissipation/Total	160	mW
Power dissipation/Chip	40	mW
Forward current	20	mA
Peak forward current	60*	mA
Reverse voltage	4	V
Operating temperature	-25 ~ +85	$^\circ\text{C}$
Storage temperature	-55 ~ +100	$^\circ\text{C}$

Orange SBD 446SR (GaAsP/GaP)

Absolute Maximum Ratings ($T_a=25^\circ\text{C}$)

Power dissipation/Total	160	mW
Power dissipation/Chip	40	mW
Forward current	20	mA
Peak forward current	60*	mA
Reverse voltage	4	V
Operating temperature	-25 ~ +85	$^\circ\text{C}$
Storage temperature	-55 ~ +100	$^\circ\text{C}$

Yellow-green SBD 446UG (GaP)

Absolute Maximum Ratings ($T_a=25^\circ\text{C}$)

Power dissipation/Total	160	mW
Power dissipation/Chip	40	mW
Forward current	20	mA
Peak forward current	60*	mA
Reverse voltage	4	V
Operating temperature	-25 ~ +85	$^\circ\text{C}$
Storage temperature	-55 ~ +100	$^\circ\text{C}$

Yellow SBD 446Y (GaAsP/GaP)

Absolute Maximum Ratings ($T_a=25^\circ\text{C}$)

Power dissipation/Total	160	mW
Power dissipation/Chip	40	mW
Forward current	20	mA
Peak forward current	60*	mA
Reverse voltage	4	V
Operating temperature	-25 ~ +85	$^\circ\text{C}$
Storage temperature	-55 ~ +100	$^\circ\text{C}$

Electrical/Optical Characteristics ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Conditions	Min	Typ	Max.	Unit
Forward voltage/Chip	V_F	$I_F = 10\text{mA}$	—	2.1	2.3	V
Reverse current/Chip	I_R	$V_R = 4\text{V}$	—	—	10	μA
Luminous Intensity/Chip	I_V	$I_F = 10\text{mA}$	300	800	—	μcd
Peak wavelength	λ_P	$I_F = 10\text{mA}$	—	700	—	nm
Spectral line halfwidth	$\Delta\lambda$	$I_F = 10\text{mA}$	—	100	—	nm

Electrical/Optical Characteristics ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Conditions	Min	Typ	Max.	Unit
Forward voltage/Chip	V_F	$I_F = 10\text{mA}$	—	2.1	2.3	V
Reverse current/Chip	I_R	$V_R = 4\text{V}$	—	—	10	μA
Luminous Intensity/Chip	I_V	$I_F = 10\text{mA}$	350	900	—	μcd
Peak wavelength	λ_P	$I_F = 10\text{mA}$	—	555	—	nm
Spectral line halfwidth	$\Delta\lambda$	$I_F = 10\text{mA}$	—	30	—	nm

Electrical/Optical Characteristics ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Conditions	Min	Typ	Max.	Unit
Forward voltage/Chip	V_F	$I_F = 10\text{mA}$	—	2.0	2.2	V
Reverse current/Chip	I_R	$V_R = 4\text{V}$	—	—	10	μA
Luminous Intensity/Chip	I_V	$I_F = 10\text{mA}$	700	1500	—	μcd
Peak wavelength	λ_P	$I_F = 10\text{mA}$	—	635	—	nm
Spectral line halfwidth	$\Delta\lambda$	$I_F = 10\text{mA}$	—	35	—	nm

Electrical/Optical Characteristics ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Conditions	Min	Typ	Max.	Unit
Forward voltage/Chip	V_F	$I_F = 10\text{mA}$	—	2.1	2.3	V
Reverse current/Chip	I_R	$V_R = 4\text{V}$	—	—	10	μA
Luminous Intensity/Chip	I_V	$I_F = 10\text{mA}$	600	1200	—	μcd
Peak wavelength	λ_P	$I_F = 10\text{mA}$	—	565	—	nm
Spectral line halfwidth	$\Delta\lambda$	$I_F = 10\text{mA}$	—	30	—	nm

Electrical/Optical Characteristics ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Conditions	Min	Typ	Max.	Unit
Forward voltage/Chip	V_F	$I_F = 10\text{mA}$	—	2.0	2.2	V
Reverse current/Chip	I_R	$V_R = 4\text{V}$	—	—	10	μA
Luminous Intensity/Chip	I_V	$I_F = 10\text{mA}$	600	1000	—	μcd
Peak wavelength	λ_P	$I_F = 10\text{mA}$	—	585	—	nm
Spectral line halfwidth	$\Delta\lambda$	$I_F = 10\text{mA}$	—	30	—	nm

* Pulse Width 1 ms
Duty Cycle 1/5